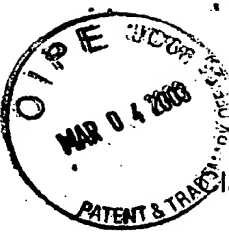


CLAIM SUMMARY DOCUMENT



Claims 1-16 (Canceled).

Claim 17 (New) An arrangement for connecting a ground connection of a semiconductor device on top of at least one layer on one side of a semiconductor substrate to ground on the reverse side of the substrate, wherein a metal plug extends through said at least one layer down into the substrate, and wherein an electrically conductive connector interconnects the ground connection and the metal plug.

Claim 18 (New) The arrangement according to claim 17, wherein said plug extends deeper into the substrate than PN junctions located therein.

Claim 19 (New) The arrangement according to claim 17, wherein the connector is a metal connector.

Claim 20 (New) The arrangement according to claim 17, wherein said semiconductor device is a high frequency device.

Claim 21 (New) The arrangement according to claim 17, wherein said semiconductor device is a power device.

Claim 22 (New) The arrangement according to claim 17, wherein said semiconductor device is a bipolar transistor and said ground connection is an emitter connection.

Claim 23 (New) The arrangement according to claim 17, wherein said device is a MOS transistor and said ground connection is a source connection.